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AMENDMENTS TO THE SPECIFICATION:

Please replace paragraph [0021] with the following rewritten paragraph:

-- In another embodiment of the present invention, the basic steps above are incorporated into [[a]] another method to form a planar hybrid-orientation SiOI substrate structure. In this method, a 110-oriented SiOI layer on a BOX layer is used for the first, lower layer of a bilayer template stack, and a 100-oriented Si layer is used for the second, upper layer of a bilayer template stack. The lowermost portion of the bilayer template stack is then amorphized in selected areas from the BOX layer up to a depth ending in the upper template layer. The amorphized Si regions are then recrystallized into 100-orientated Si, using the upper 100-oriented Si layer as a template. The uppermost portion of the bilayer template is then removed by a process such as polishing to leave coplanar surface regions of 110-oriented Si (in the untreated areas) and 100-oriented Si (in the treated areas).--